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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Complete if Known

Application Number	10/652,007
Filing Date	August 29, 2003
First Named Inventor	Sheldon Aronowitz
Group Art Unit	1765
Examiner Name	David M. Brunsman
Attorney Docket No.	/ 00-643/1D

Sheet 1 of 1

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code (if known)			
h		5,152,819		Blackwell et al.	10-06-1992	
h		5,879,649		Henderson et al.	03-09-1999	
h		6,020,458		Lee et al.	02-01-2000	
h		6,508,997		Choate et al.	01-21-2003	

Examiner signature		Date considered	2/18/05
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Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office, TO THIS ADDRESS, SEND TO: Assistant Commissioner for Patents.

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FORM PTO-1449 (Modified) U.S. Department of Commerce, Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Docket No.	Serial No.
	00-643/1D	
	Applicants	
	Sheldon Aronowitz et al.	
Filing Date Herewith	Group Unknown	

U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>l</i>	AA	5,874,367	2/23/99	Dobson	438	787	
<i>l</i>	AB	6,028,015	2/22/00	Wang et al.	438	789	3/29/99
<i>l</i>	AC	6,114,259	9/5/00	Sukharev et al.	438	789	7/27/99
<i>l</i>	AD	6,147,012	11/14/00	Sukharev et al.	438	787	11/12/99
<i>l</i>	AE	6,043,167	3/28/00	Lee et al.	438	789	10/10/97
<i>l</i>	AF	5,314,845	5/24/94	Lee et al.	437	238	2/2/90
<i>l</i>	AG	5,915,203	6/22/99	Sengupta et al.	438	669	6/10/97
<i>l</i>	AH	6,365,528	4/2/02	Sukharev et al.	438	778	6/7/00
<i>l</i>	AI	5,571,571	11/5/96	Musaka et al.	427	574	6/14/94
<i>l</i>	AJ	6,303,047	10/16/01	Aronowitz et al.	252	1	3/22/99
<i>l</i>	AK	6,511,925	1/28/03	Aronowitz et al.	438	788	10/19/01

Foreign Patent Documents							
							Translation
		Document Number	Date	Country	Class	Subclass	Yes No
	AL						
	AM						
	AN						
	AO						
	AP						

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
<i>l</i>	AR	Bothra, S., et al., "Integration of 0.25 μ m Three and Five Level Interconnect System for High Performance ASIC", <u>1997 Proceedings Fourteenth International VMIC Conference</u> , Santa Clara, CA, June 10-12, 1997, pp.43-48.
<i>l</i>	AS	Dobson, C.D., et al., "Advanced SiO ₂ Planarization Using Silane and H ₂ O ₂ ", <u>Semiconductor International</u> , December 1994, pp. 85-88.
<i>l</i>	AT	McClatchie, S., et al., "Low Dielectric Constant Oxide Films Deposited Using CVD Techniques", <u>1998 Proceedings Fourth International DUMIC Conference</u> , February 16-17, 1998, pp. 311-318.

Examiner <i>Shelley</i>	Date Considered <i>2/18/01</i>
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.	

FORM PTO-1449 (Modified) U.S. Department of Commerce, Patent and Trademark Office					Docket No. 00-643/1D		Serial No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)					Applicants Sheldon Aronowitz et al.			
					Filing Date Herewith		Group Unknown	

U.S. Patent Documents							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
r	BA	6,066,574	5,23/00	You et al.	438	781	11/6/98
a	BB	6,051,477	4/18/00	Nam	438	404	10/22/96
h	BC	6,025,263	2/15/00	Tsai et al.	438	624	9/11/97
a	BD	5,939,763	8/17/99	Hao et al.	257	411	9/5/96
h	BE	5,864,172	1/26/99	Kapoor et al.	257	634	8/13/96
h	BF	5,688,724	11/18/97	Yoon et al.	437	235	12/23/94
h	BG	5,470,801	11/28/95	Kapoor et al.	437	238	6/28/93
h	BH	5,364,800	11/15/94	Joyner	437	28	6/24/93
h	BI	4,771,328	9/13/88	Malaviya et al.	357	49	11/24/86
h	BJ	3,652,331	3/28/72	Yamazaki	117	201	3/13/69
	BK						

Foreign Patent Documents							
							Translation
	Document Number	Date	Country	Class	Subclass	Yes	No
	BL						
	BM						
	BN						
	BO						
	BP						

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
a	BR	Nguyen, S. et al., "Reaction Mechanisms of Plasma- and Thermal-Assisted Chemical Vapor Deposition of Tetraethylorthosilicate Oxide Films", <u>J. Electrochem. Soc.</u> , Vol. 137, No. 7, July, 1990, pp. 2209-2215.
h	BS	Peters, Laura, "Low-k Dielectrics: Will Spin-On or CVD Prevail?", <u>Semiconductor International</u> , Vol. 23, No. 6, June, 2000, pp. 108-110, 114, 116, 118, 122, and 124.
h	BT	Peters, Laura, "Pursuing the Perfect Low-k Dielectric", <u>Semiconductor International</u> , Vol. 21, No. 10, September, 1998, pp. 64-66, 68, 70, 72, and 74.

Examiner <i>gklyn</i>	Date Considered <i>2/18/05</i>
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	00-643/1D	
	Applicants	
	Sheldon Aronowitz et al.	
Filing Date Herewith	Group Unknown	

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
g	CA	6,153,524	11/28/00	Henley et al.	438	691	7/28/98
K	CB	6,051,073	4/18/00	Chu et al.	118	723	6/3/98
h	CC	5,580,429	12/3/96	Chan et al.	204	192.38	6/7/95
a	CD	5,558,718	9/24/96	Leung	118	723E	4/8/94
v	CE	5,628,871	5/13/97	Shinagawa	438	514	6/24/94
h	CF	6,204,192	3/20/01	Zhao et al.	438	723	3/29/99
1	CG	6,232,658	5/15/01	Catabay et al.	257	701	6/30/99
n	CH	6,037,248	3/14/00	Ahn	438	619	6/13/97
h	CI	5,675,187	10/7/97	Numata et al.	257	758	5/16/96
h	CJ	5,559,367	9/24/96	Cohen et al.	257	77	7/12/94
c	CK	5,376,595	12/27/94	Zupancic et al.	501	12	8/28/92

Foreign Patent Documents

Translation

		Document Number	Date	Country	Class	Subclass	Yes	No
c	CL	2000-267128	9/29/00	Japan	G02F	1/136	X-Abstract Only	
	CM							
	CN							
	CO							
	CP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

a	CR	Sugahara, Satoshi, et al., "Chemical Vapor Deposition of CF ₃ -Incorporated Silica Films for Interlayer Dielectric Application", 1999 Joint International Meeting, <u>Electrochemical Society Meeting Abstracts</u> , Vol. 99-2, 1999, Abstract No. 746.
v	CS	Koda, Seiichiro, et al., "A Study of Inhibition Effects for Silane Combustion by Additive Gases", <u>Combustion and Flame</u> , Vol. 73, No. 2, August, 1988, pp. 187-194.
	CT	

Examiner

Date Considered

2/18/05

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FORM PTO-1449 (Modified)
U.S. Department of Commerce, Patent and Trademark Office

Docket No.

00-643

Serial No.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

Applicants

Sheldon Aronowitz et al.

Filing Date
HerewithGroup
Unknown

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
A	DA	5,904,154	5/18/99	Chien et al.	134	1.2	7/24/97
a	DB	5,882,489	3/16/99	Bersin et al.	204	192.35	4/26/96
A	DC	5,858,879	1/12/99	Chao et al.	438	725	6/6/97
A	DD	3,012,861	12/12/61	Ling	23	223.5	1/15/60
u	DE	3,178,392	4/13/65	Kriner	260	46.5	4/9/62
a	DF	3,832,202	8/27/74	Ritchie	106	287	8/8/72
A	DG	3,920,865	11/18/75	Läufer et al.	427	220	4/6/72
A	DH	4,705,725	11/10/87	Glaich et al.	428	405	11/28/86
A	DI	5,194,333	3/16/93	Ohnaka et al.	428	405	12/18/90
A	DJ	5,874,745	2/23/99	Kuo	257	59	8/5/97
	DK						

Foreign Patent Documents

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		Document Number	Date	Country	Class	Subclass	Yes	No
T	DL	DE 198 04 375 A1	7/1/99	Germany	H 01 L	21/312		X
a	DM	EP 0 706 216 A2	4/10/96	Europe	H 01 L	23/532	N/A	
u	DN	EP 0 949 663 A2	10/13/99	Europe	H 01 L	21/312	N/A	
A	DO	63003437	1/8/88	Japan	H 01 L	21/90	X-Abstract Only	
A	DP	WO 99/41423	8/19/99	PCT	C 23 C		N/A	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	DR	
	DS	
	DT	

Examiner

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2/18/08

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